

# NSP8814, NSP8818

## ESD and Surge Protection Device

### Low Capacitance Surge Protection for High Speed Data

The NSP8814 and NSP8818 surge protectors are designed specifically to protect 10/100 and GbE Ethernet signals from high levels of surge current. Low clamping voltage under high surge conditions make this device an ideal solution for protecting voltage sensitive lines leading to Ethernet transceiver chips. Low capacitance combined with flow-through style packaging allows for easy PCB layout and matched trace lengths necessary to maintain consistent impedance between high-speed differential lines.

#### Features

- Protection for the Following IEC Standards:
  - IEC 61000-4-2 (ESD)  $\pm 30$  kV (Contact)
  - IEC 61000-4-5 (Lightning) 35 A (8/20  $\mu$ s)
- Flow-Thru Routing Scheme
- Low Capacitance: 2 pF Max (I/O to I/O)
- UL Flammability Rating of 94 V-0
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### Typical Applications

- 10/100 and GbE Ethernet
- MagJacks® / Integrated Magnetics
- Notebooks/Desktops/Servers

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

| Rating                                                                                                             | Symbol    | Value                | Unit             |
|--------------------------------------------------------------------------------------------------------------------|-----------|----------------------|------------------|
| Operating Junction Temperature Range                                                                               | $T_J$     | -55 to +125          | $^\circ\text{C}$ |
| Storage Temperature Range                                                                                          | $T_{stg}$ | -55 to +150          | $^\circ\text{C}$ |
| Lead Solder Temperature – Maximum (10 Seconds)                                                                     | $T_L$     | 260                  | $^\circ\text{C}$ |
| IEC 61000-4-2 Contact (ESD)<br>IEC 61000-4-2 Air (ESD)                                                             | ESD       | $\pm 30$<br>$\pm 30$ | kV               |
| Maximum Peak Pulse Current<br>8/20 $\mu$ s @ $T_A = 25^\circ\text{C}$<br>10/700 $\mu$ s @ $T_A = 25^\circ\text{C}$ | $I_{pp}$  | 35<br>20             | A                |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

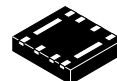
See Application Note AND8308/D for further description of survivability specs.



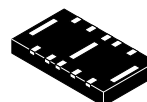
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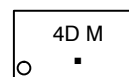
#### MARKING DIAGRAMS



UDFN8  
CASES 506CV



UDFN10  
CASE 506CU



XX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

#### ORDERING INFORMATION

| Device       | Package             | Shipping           |
|--------------|---------------------|--------------------|
| NSP8814MUTAG | UDFN8<br>(Pb-Free)  | 3000 / Tape & Reel |
| NSP8818MUTAG | UDFN10<br>(Pb-Free) | 3000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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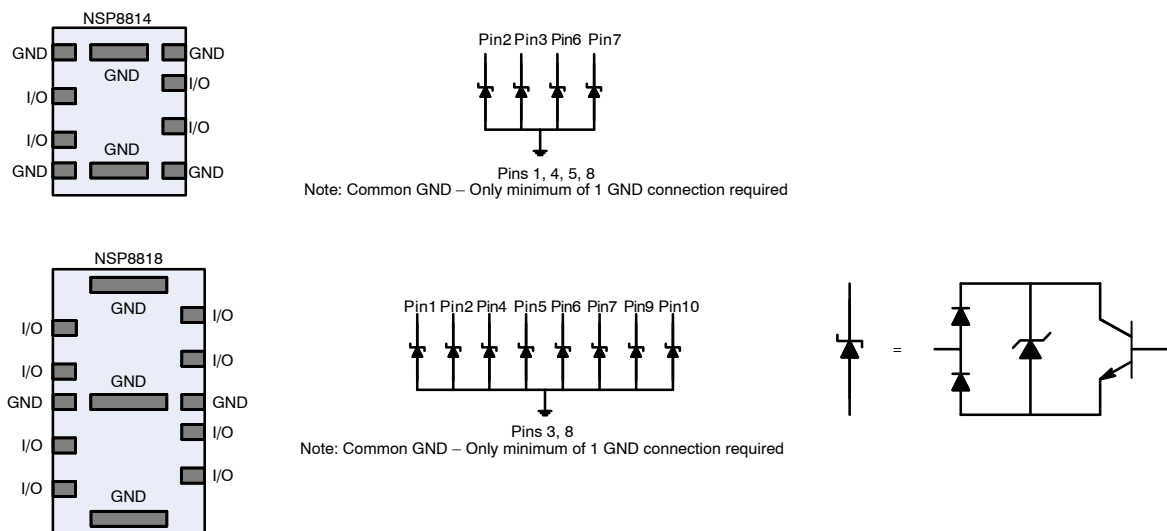
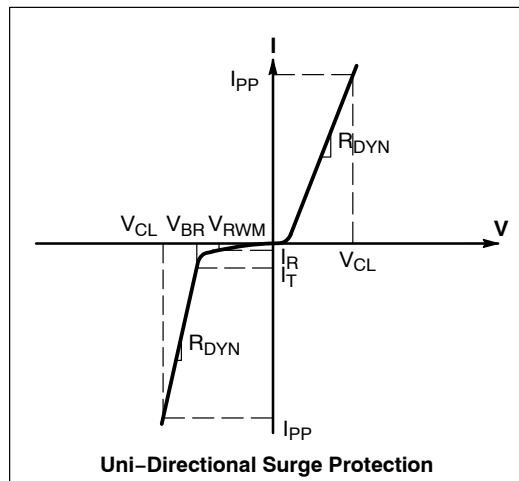


Figure 1. Pin Schematic

## ELECTRICAL CHARACTERISTICS

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

| Symbol     | Parameter                                                            |
|------------|----------------------------------------------------------------------|
| $V_{RWM}$  | Working Peak Voltage                                                 |
| $I_R$      | Maximum Reverse Leakage Current @ $V_{RWM}$                          |
| $V_{BR}$   | Breakdown Voltage @ $I_T$                                            |
| $I_T$      | Test Current                                                         |
| $V_{HOLD}$ | Holding Reverse Voltage                                              |
| $I_{HOLD}$ | Holding Reverse Current                                              |
| $R_{DYN}$  | Dynamic Resistance                                                   |
| $I_{PP}$   | Maximum Peak Pulse Current                                           |
| $V_C$      | Clamping Voltage @ $I_{PP}$<br>$V_C = V_{HOLD} + (I_{PP} * R_{DYN})$ |



## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise specified)

| Parameter                 | Symbol    | Conditions                                                                                              | Min                  | Typ                     | Max                    | Unit          |
|---------------------------|-----------|---------------------------------------------------------------------------------------------------------|----------------------|-------------------------|------------------------|---------------|
| Reverse Working Voltage   | $V_{RWM}$ | Any I/O to GND (Note 1)                                                                                 |                      |                         | 3.0                    | V             |
| Forward Voltage           | $V_F$     | $I_F = 10 \text{ mA}$ , GND to All IO Pins                                                              | 0.5                  | 0.85                    | 1.1                    | V             |
| Breakdown Voltage         | $V_{BR}$  | $I_T = 1 \text{ mA}$ , I/O to GND                                                                       | 3.2                  | 3.5                     | 5.0                    | V             |
| Reverse Leakage Current   | $I_R$     | $V_{RWM} = 3.0 \text{ V}$ , I/O to GND                                                                  |                      |                         | 0.5                    | $\mu\text{A}$ |
| Clamping Voltage (Note 2) | $V_C$     | $I_{PP} = 1 \text{ A}$<br>$I_{PP} = 10 \text{ A}$<br>$I_{PP} = 25 \text{ A}$<br>$I_{PP} = 35 \text{ A}$ |                      | 4.0<br>6.0<br>8.0<br>10 | 5.0<br>6.5<br>10<br>15 | V             |
| Clamping Voltage          | $V_C$     | IEC61000-4-2, $\pm 8 \text{ kV}$ Contact                                                                | See Figures 7 and 14 |                         |                        | V             |
| Junction Capacitance      | $C_J$     | $V_R = 0 \text{ V}$ , $f = 1 \text{ MHz}$ between I/O Pins                                              |                      | 1.5                     | 2.0                    | pF            |
|                           |           | $V_R = 0 \text{ V}$ , $f = 1 \text{ MHz}$ between I/O Pins and GND                                      |                      |                         | 5.0                    |               |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Surge protection devices are normally selected according to the working peak reverse voltage ( $V_{RWM}$ ), which should be equal or greater than the DC or continuous peak operating voltage level.
- Any I/O to GND (8/20  $\mu\text{s}$  pulse).

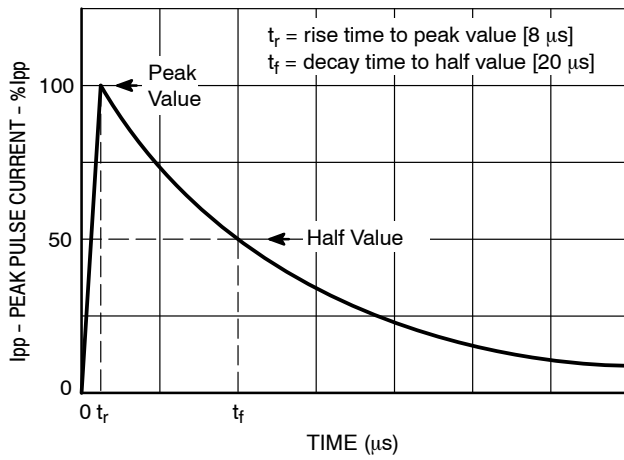


Figure 2. IEC61000-4-5 8/20  $\mu$ s Pulse Waveform

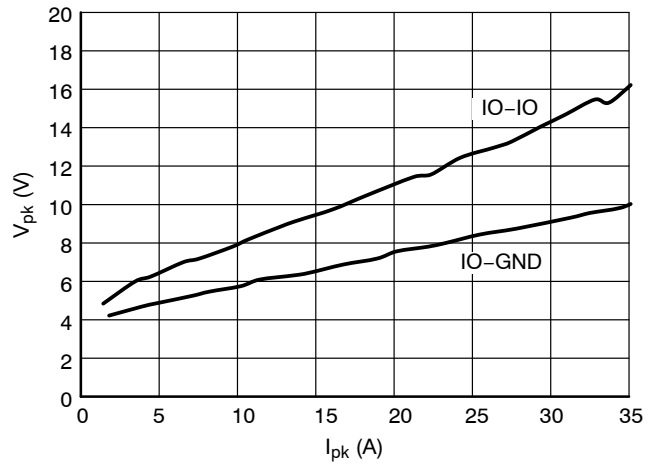


Figure 3. Clamping Voltage vs. Peak Pulse Current ( $t_p = 8/20 \mu$ s per Figure 2)

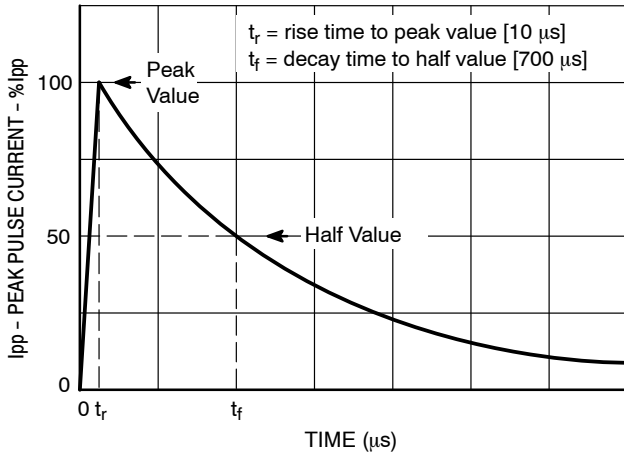


Figure 4. IEC61000-4-5 10/700  $\mu$ s Pulse Waveform

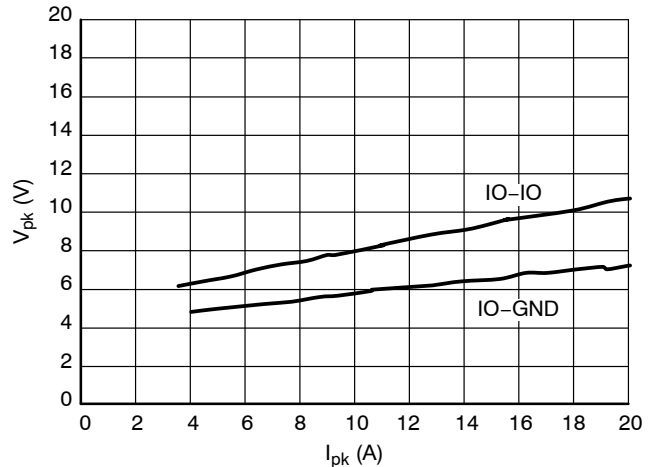


Figure 5. Clamping Voltage vs. Peak Pulse Current ( $t_p = 10/700 \mu$ s per Figure 4)

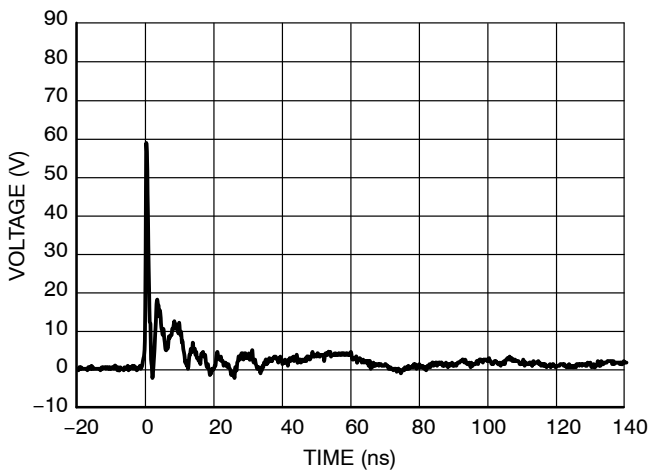


Figure 6. IEC61000-2-4 +8 kV Contact Clamping Voltage

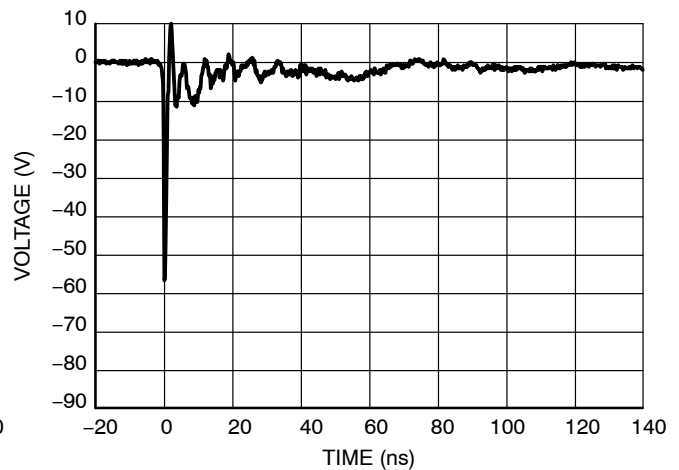


Figure 7. IEC61000-2-4 -8 kV Contact Clamping Voltage

IEC 61000-4-2 Spec.

| Level | Test Voltage (kV) | First Peak Current (A) | Current at 30 ns (A) | Current at 60 ns (A) |
|-------|-------------------|------------------------|----------------------|----------------------|
| 1     | 2                 | 7.5                    | 4                    | 2                    |
| 2     | 4                 | 15                     | 8                    | 4                    |
| 3     | 6                 | 22.5                   | 12                   | 6                    |
| 4     | 8                 | 30                     | 16                   | 8                    |

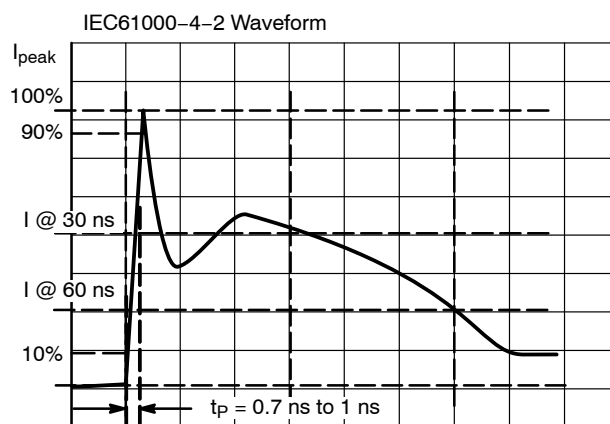


Figure 8. IEC61000-4-2 Spec

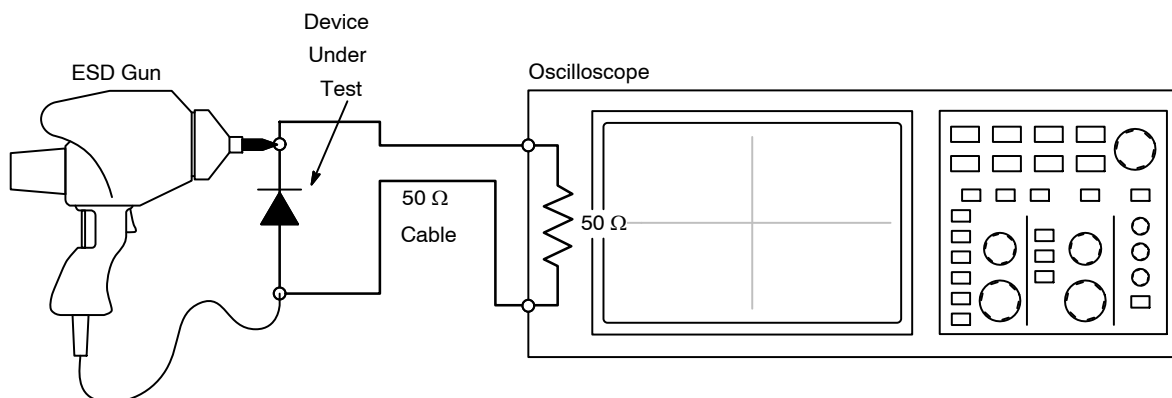


Figure 9. Diagram of ESD Clamping Voltage Test Setup

The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

**ESD Voltage Clamping**

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

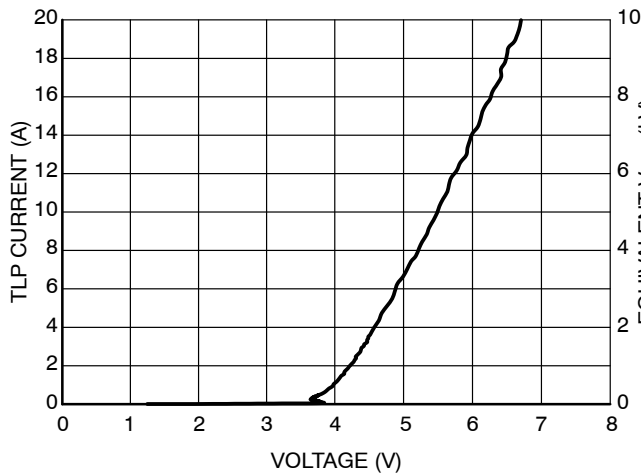


Figure 10. Positive TLP IV Curve

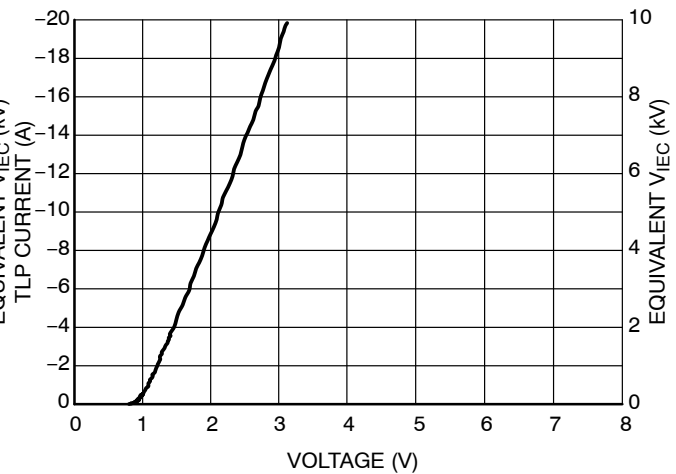


Figure 11. Negative TLP IV Curve

NOTE: TLP parameter:  $Z_0 = 50 \Omega$ ,  $t_p = 100$  ns,  $t_r = 300$  ps, averaging window:  $t_1 = 30$  ns to  $t_2 = 60$  ns.

### Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I-V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 12. TLP I-V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 13 where an 8 kV IEC 61000-4-2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I-V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels.

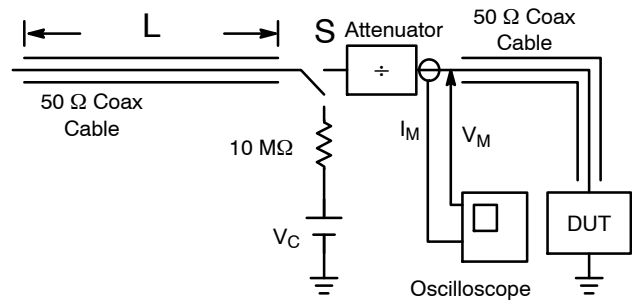


Figure 12. Simplified Schematic of a Typical TLP System

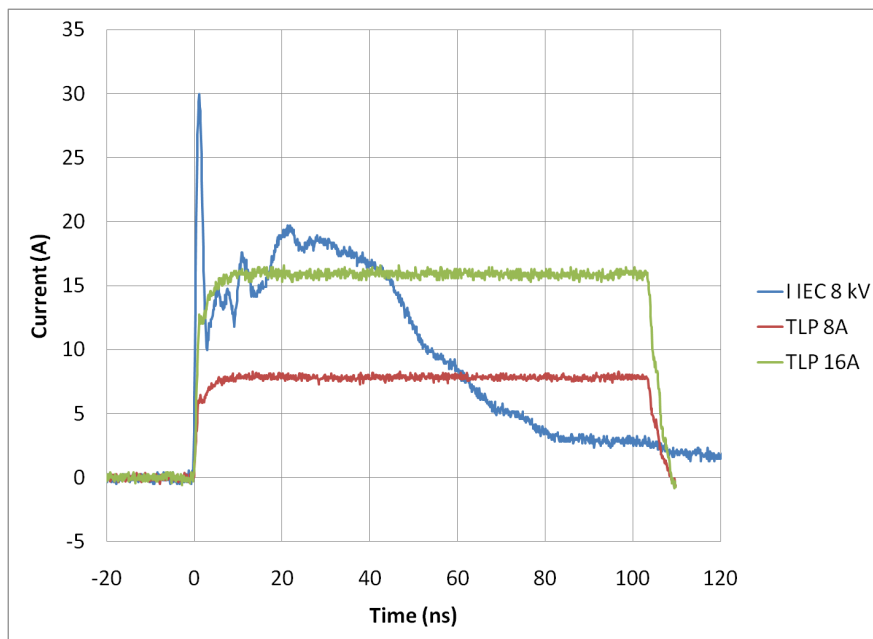


Figure 13. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms

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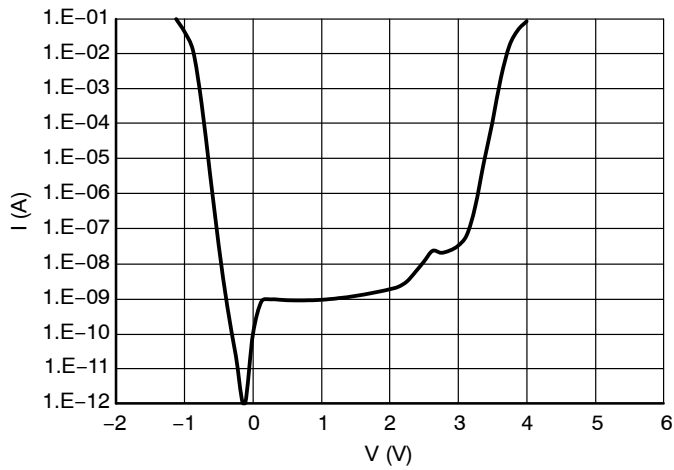


Figure 14. IV Characteristics

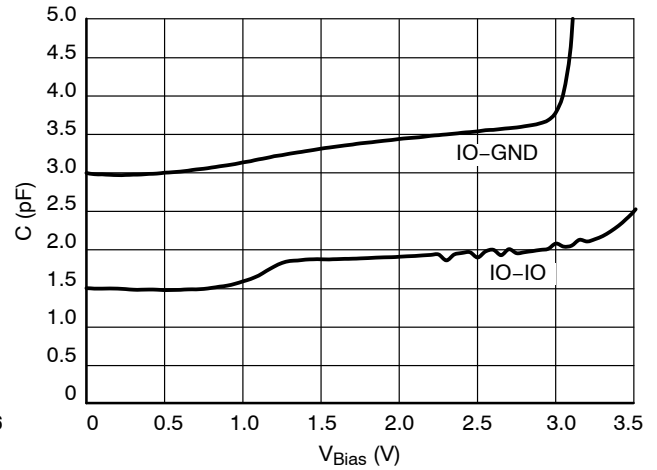


Figure 15. CV Characteristics

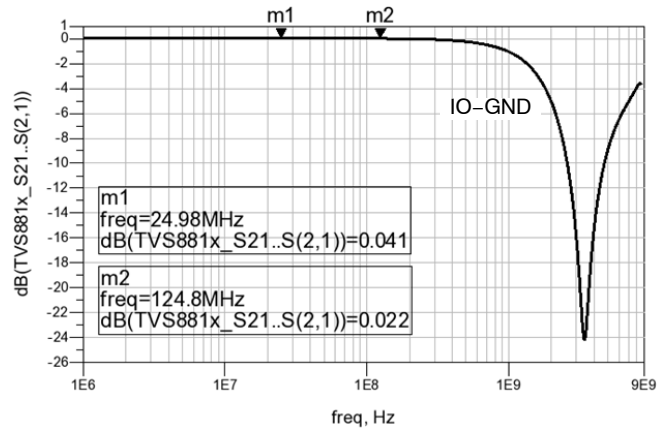


Figure 16. RF Insertion Loss

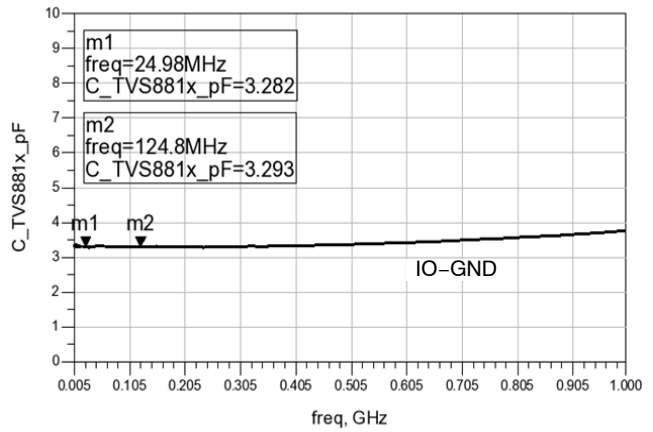


Figure 17. Capacitance Over Frequency

## NSP8814, NSP8818

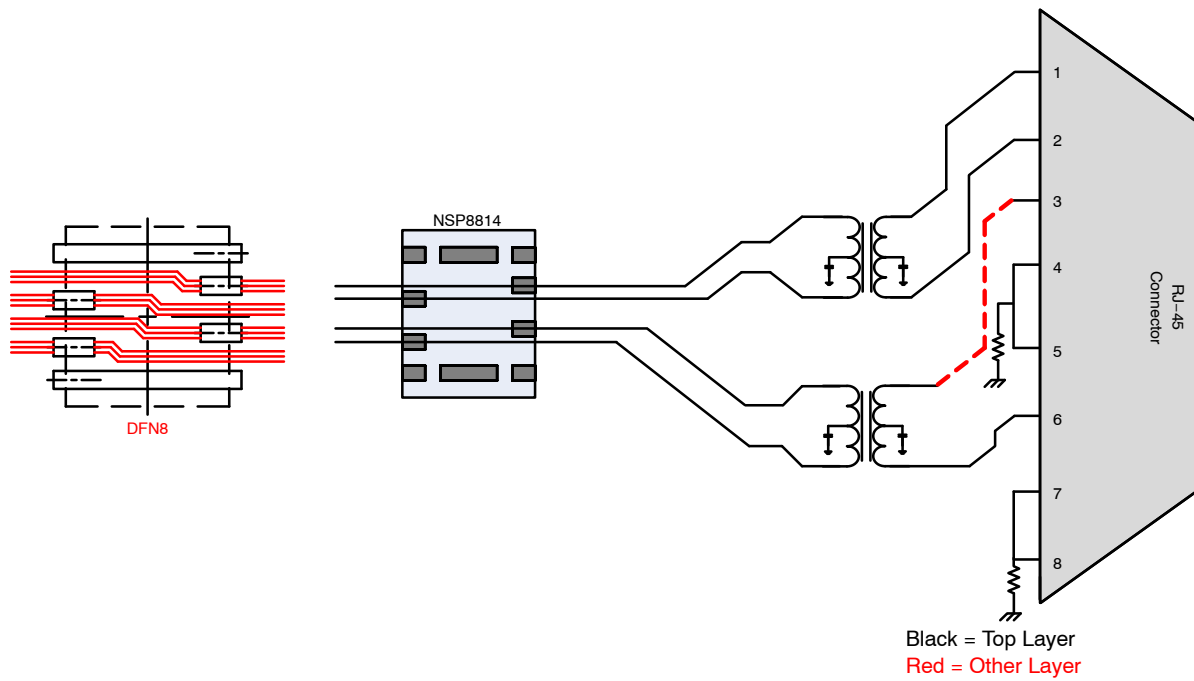


Figure 18. 10/100 Ethernet Layout Diagram and Flow-thru Routing Scheme

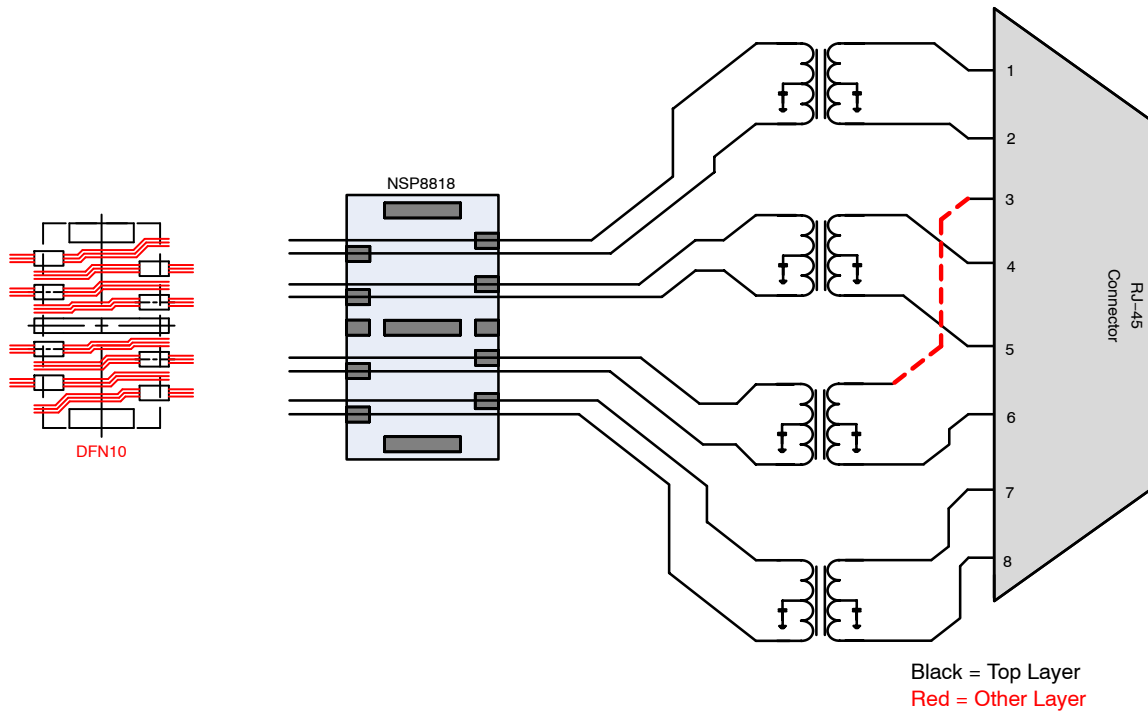


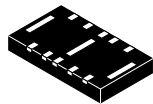
Figure 19. GbE Ethernet Layout Diagram and Flow-thru Routing Scheme

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

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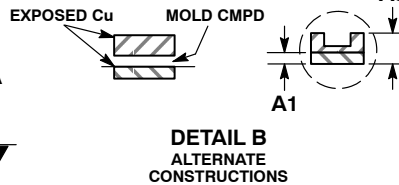
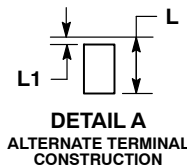
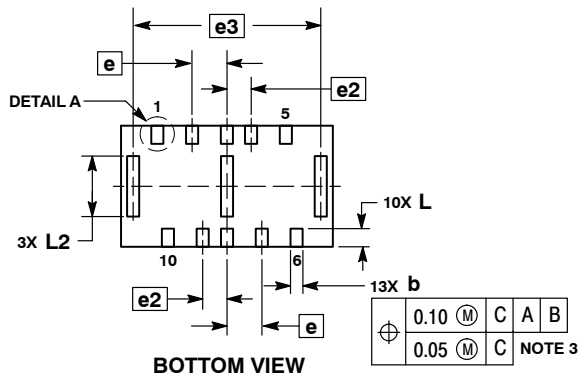
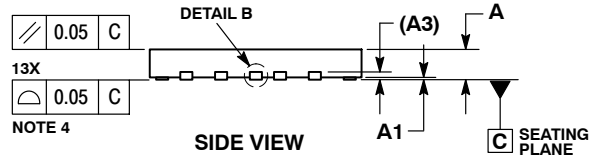
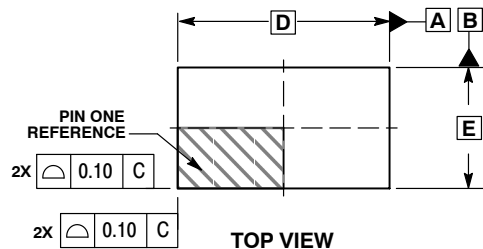
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UDFN10 3.5x2, 0.575P  
CASE 506CU  
ISSUE O

DATE 05 NOV 2013

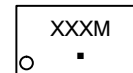


### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.25 MM FROM TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

| DIM | MILLIMETERS |      |
|-----|-------------|------|
|     | MIN         | MAX  |
| A   | 0.45        | 0.55 |
| A1  | 0.00        | 0.05 |
| A3  | 0.127       | REF  |
| b   | 0.15        | 0.25 |
| D   | 3.50        | BSC  |
| E   | 2.00        | BSC  |
| e   | 0.575       | BSC  |
| e2  | 0.40        | BSC  |
| e3  | 3.10        | BSC  |
| L   | 0.25        | 0.35 |
| L1  | 0.05        | 0.15 |
| L2  | 0.95        | 1.05 |

### GENERIC MARKING DIAGRAM\*



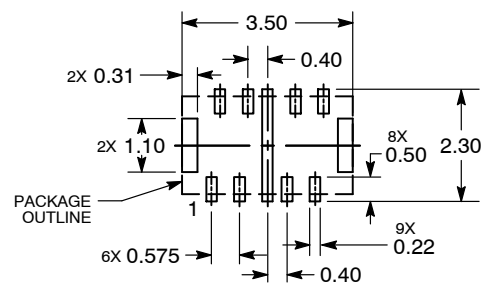
XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

### RECOMMENDED MOUNTING FOOTPRINT



DIMENSIONS: MILLIMETERS

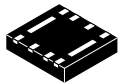
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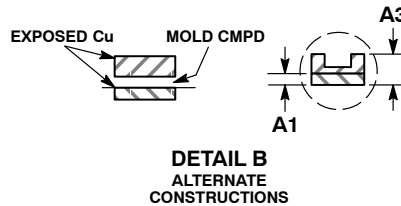
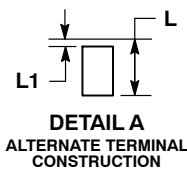
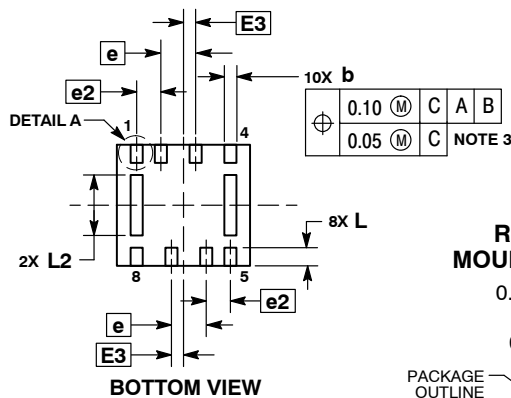
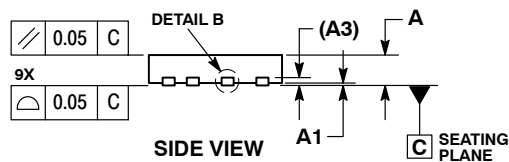
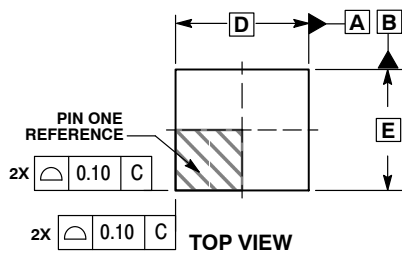
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## UDFN8 2.2x2, 0.575P CASE 506CV ISSUE A

DATE 21 JUL 2015



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
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| D           | 2.20 BSC  |      |
| E           | 2.00 BSC  |      |
| E3          | 0.20 BSC  |      |
| e           | 0.575 BSC |      |
| e2          | 0.40 BSC  |      |
| L           | 0.25      | 0.35 |
| L1          | 0.05      | 0.15 |
| L2          | 0.95      | 1.05 |

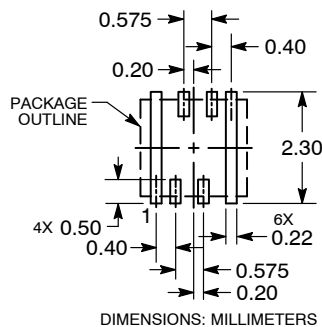
### GENERIC MARKING DIAGRAM\*



XX = Specific Device Code  
M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking.  
Pb-Free indicator, "G" or microdot "▪", may or may not be present.

### RECOMMENDED MOUNTING FOOTPRINT



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